

B-DOOR

[TERMINAL-[20020325.LOG]]

25.03.2002/13:32:06

- 2/4 - (C) WFI / DERWENT  
AN - 1997-219045 (20)  
AP - JP19950218861 19950823  
PR - JP19950218861 19950828  
TI - III-V group compound semiconductor light emitting element - has P type layer whose composition contains indium, gallium, aluminium and zinc satisfying specific relation  
IW - GROUP COMPOUND SEMICONDUCTOR LIGHT EMIT ELEMENT P TYPE LAYER COMPOSITION CONTAIN INDIUM GALLIUM ALUMINIUM ZINC SATISFY SPECIFIC RELATED  
PA - (SUMO ) SUMITOMO CHEM CO LTD  
PN - JP9064419 A 19970307 DW199720 H01L33/00 006pp  
IC - H01L21/205 ; H01L29/205 ; H01L33/00  
AB - J09064419 The element has a substrate (1) on which a buffer layer (2) is formed. A n-type layer (3) is arranged above the buffer layer. A pair of undoped layers (4,6) are arranged orderly on the n type layer between which a light emitting layer (5) is formed.  
- The undoped layers have a larger band width than the light emitting layer. A p type layer (7) is provided above one of the undoped layer. This has a composition  $In_x Ga_y Al_z N$  where  $x+y+z=1$ ,  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0.001 \leq z \leq 0.10$ .  
- ADVANTAGE - Raises luminous efficiency.  
- (Dwg.1/2)